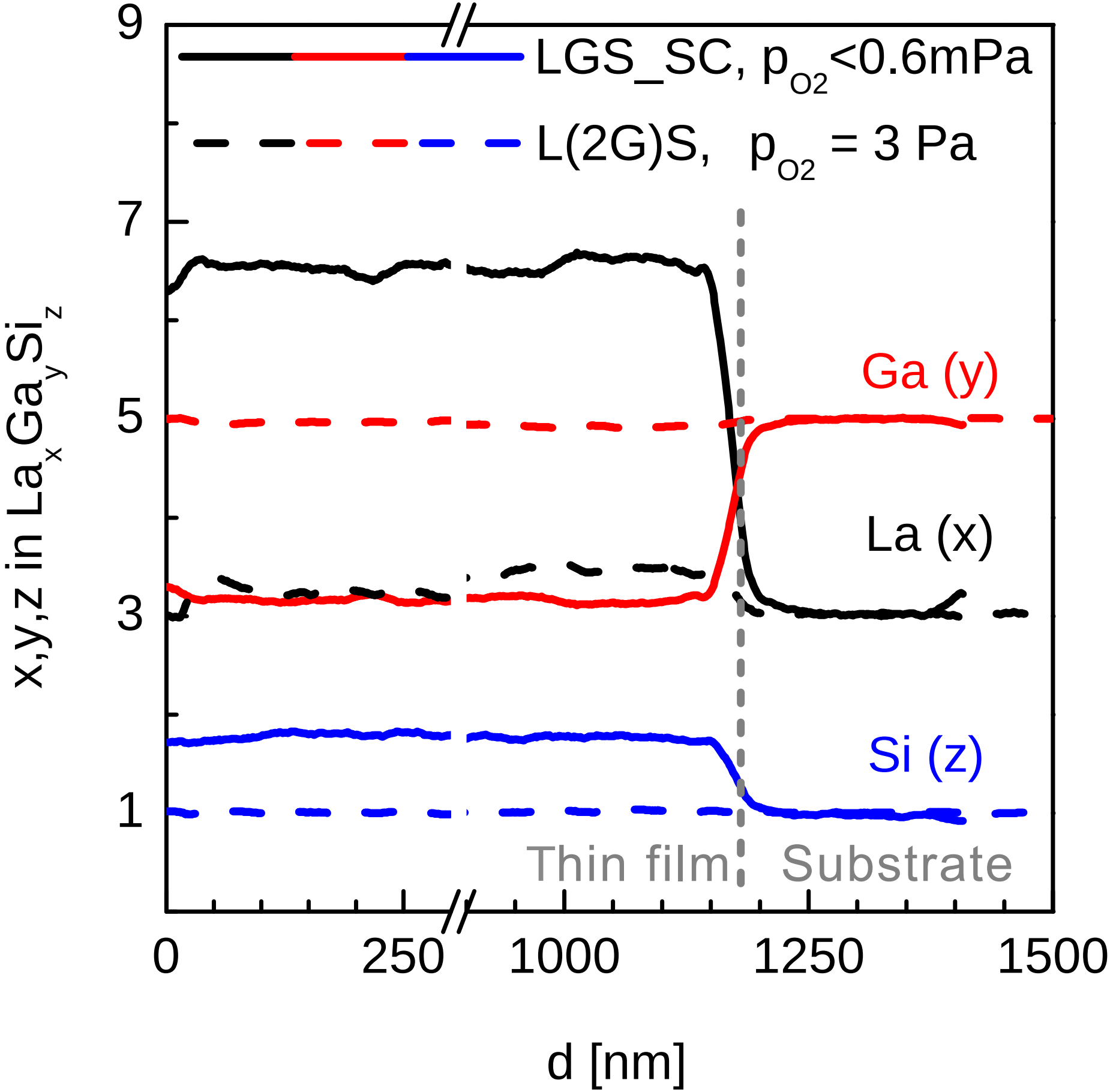
LGS_SC, p_{O2}<0.6mPa
L(2G)S, p_{O2} = 3 Pa
Ga (y)
La (x)
Si (z)
Thin film
Substrate
x,y,z in $La_xGa_ySi_z$
d [nm]
9
7
5
3
1
0
250
1000
1250
1500